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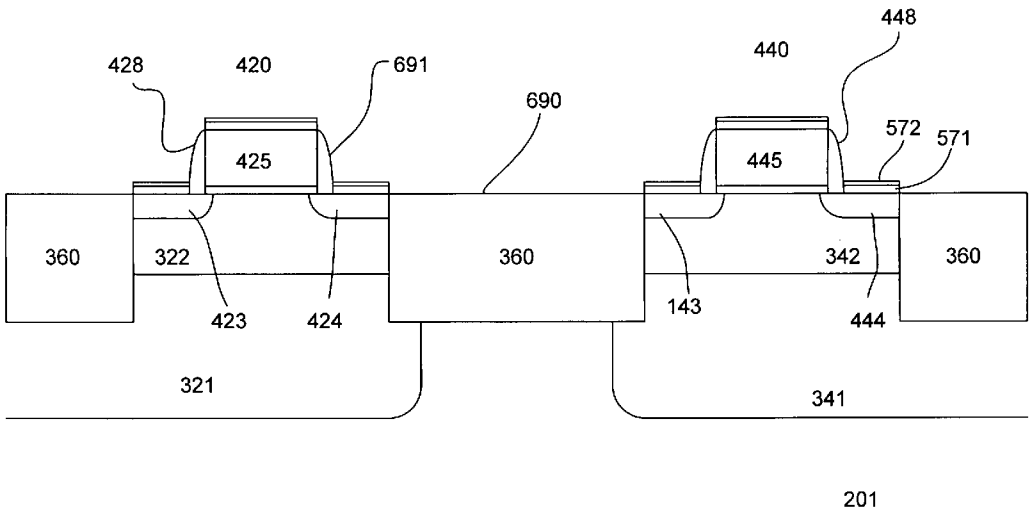
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*[Continued on next page]*

(54) Title: RELIABLE CONTACTS




(57) Abstract: A nickel-based germanide contact includes a processing material that inhibits agglomeration of nickel-based germanide during processing to form the contact as well as during post-germanidation processes. The processing material is either in the form of a capping layer over the nickel layer or integrated into the nickel layer used to form the nickel-based contact. Reducing agglomeration improves electrical characteristics of the contact.

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